

**Study of the Morphological, Optical, Structural and Electrical Properties of Silicon
Nanowires at Varying Concentration of Catalyst Precursor**

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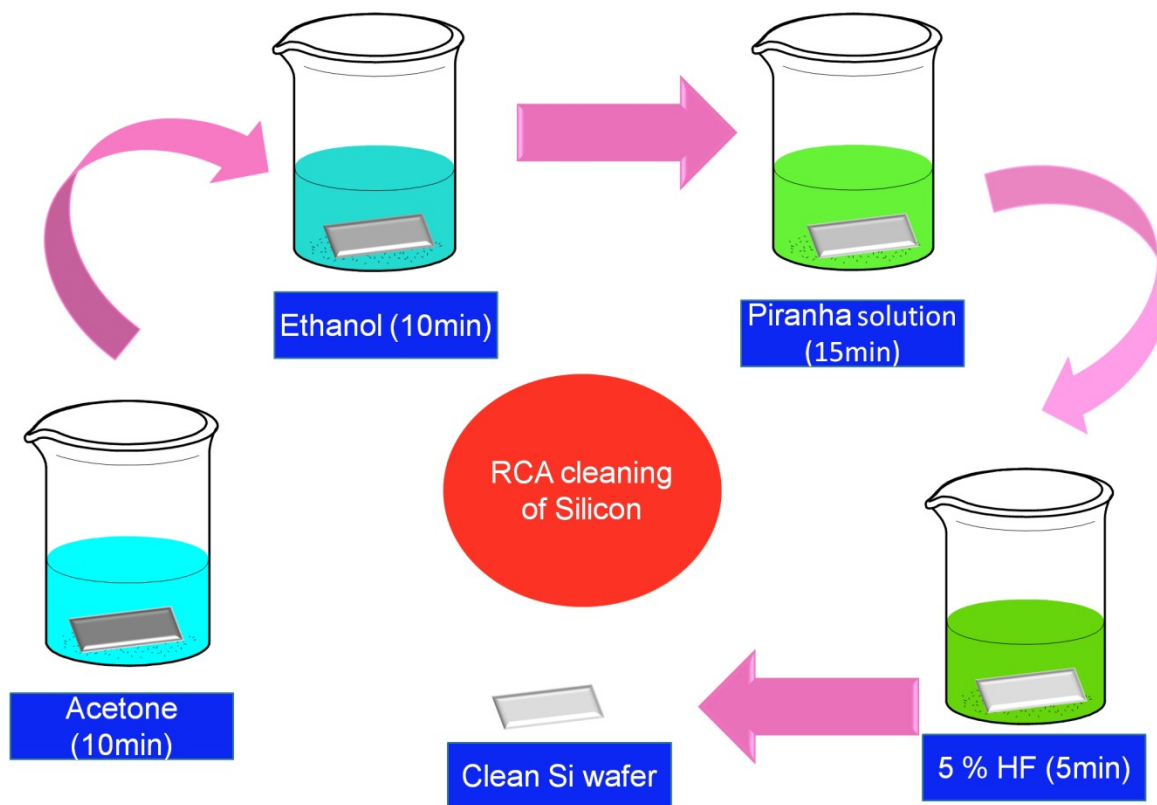


Fig. S1. RCA cleaning procedure for Si wafer

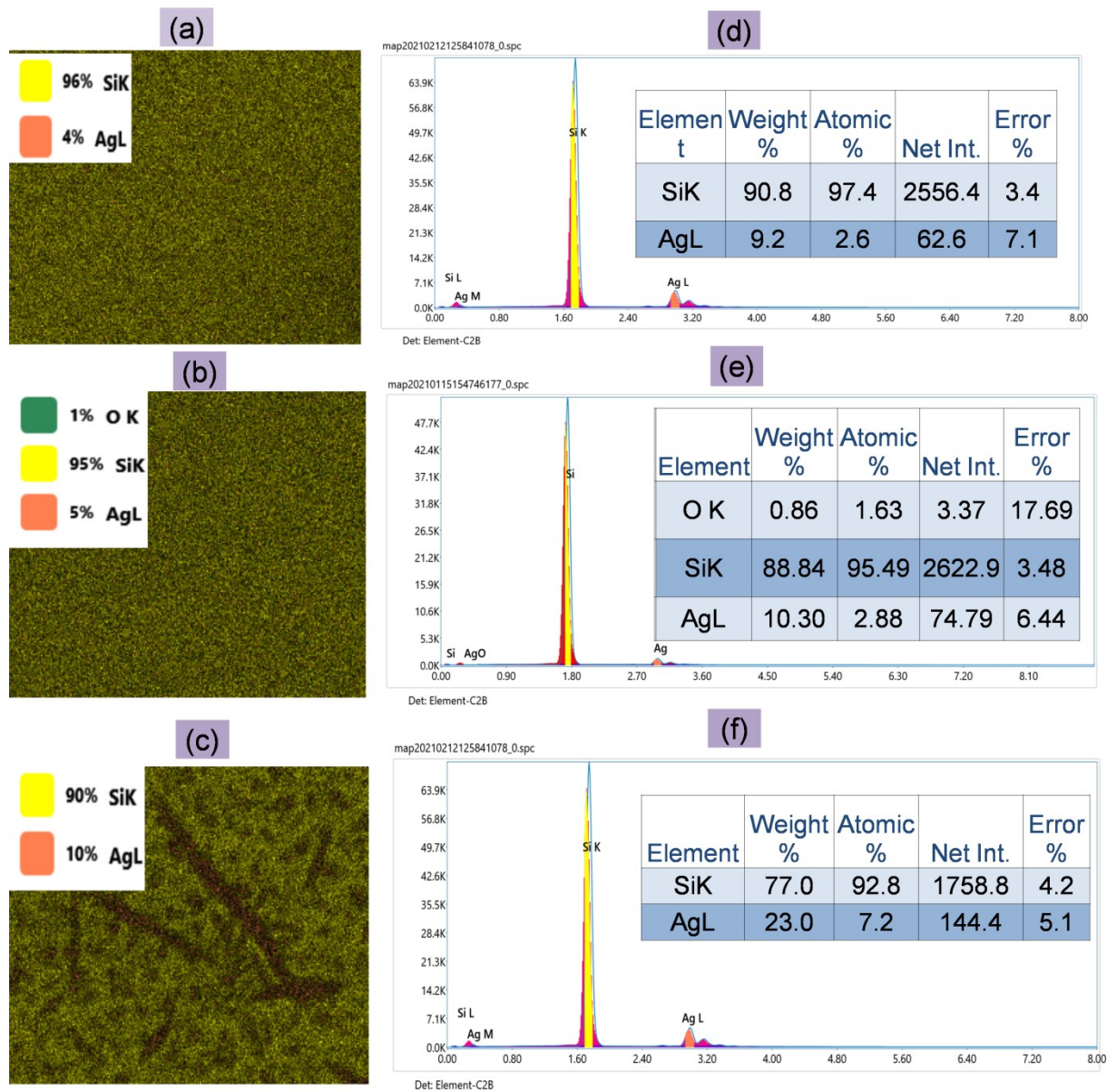


Fig S2. Elemental mapping of (a) 10A, (b) 20A and (c) 30A. EDX spectra of (d) 10A, (e) 20A and (f) 30A.

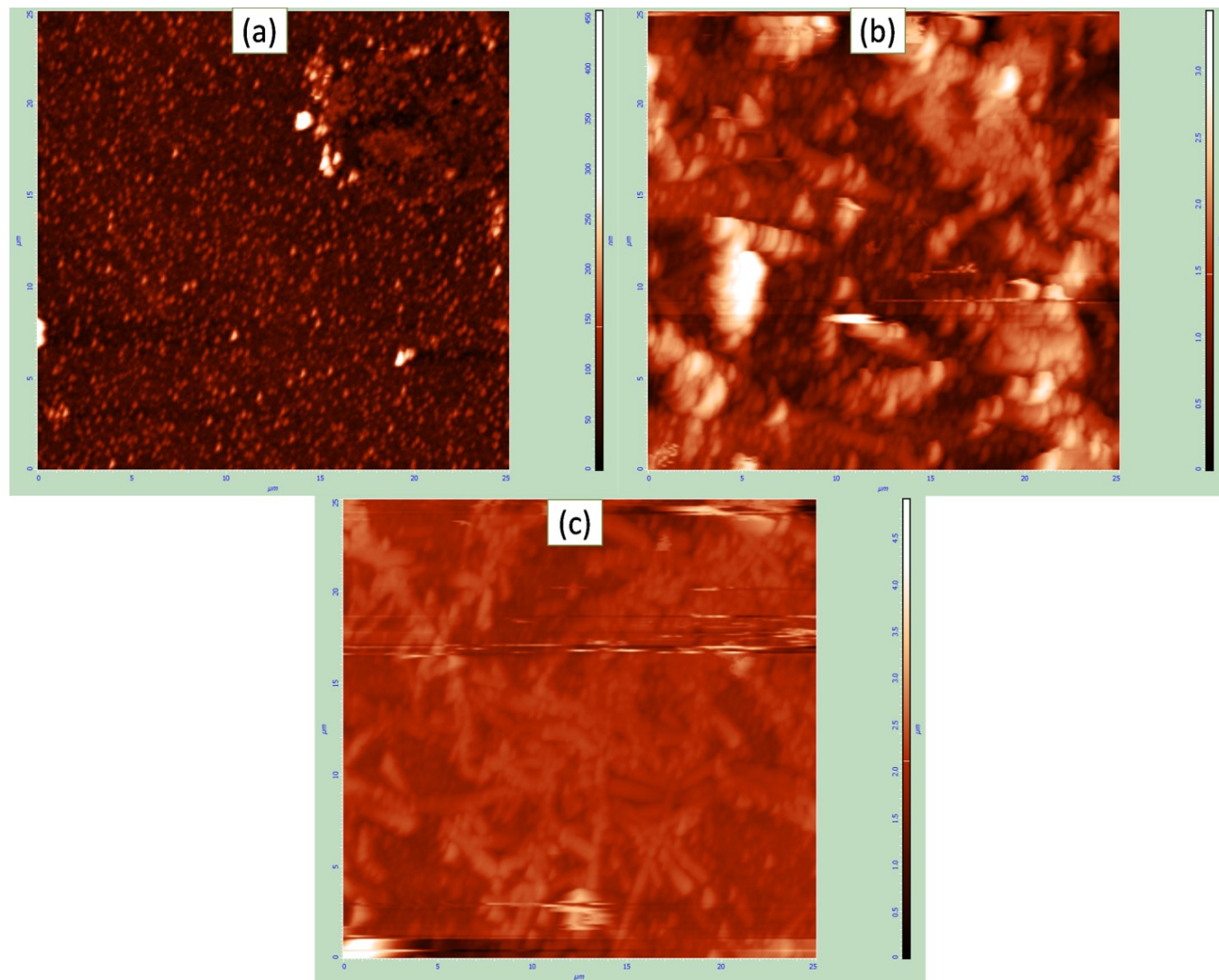


Fig S3. AFM images of (a) 10A, (b) 20A and (c) 30A.

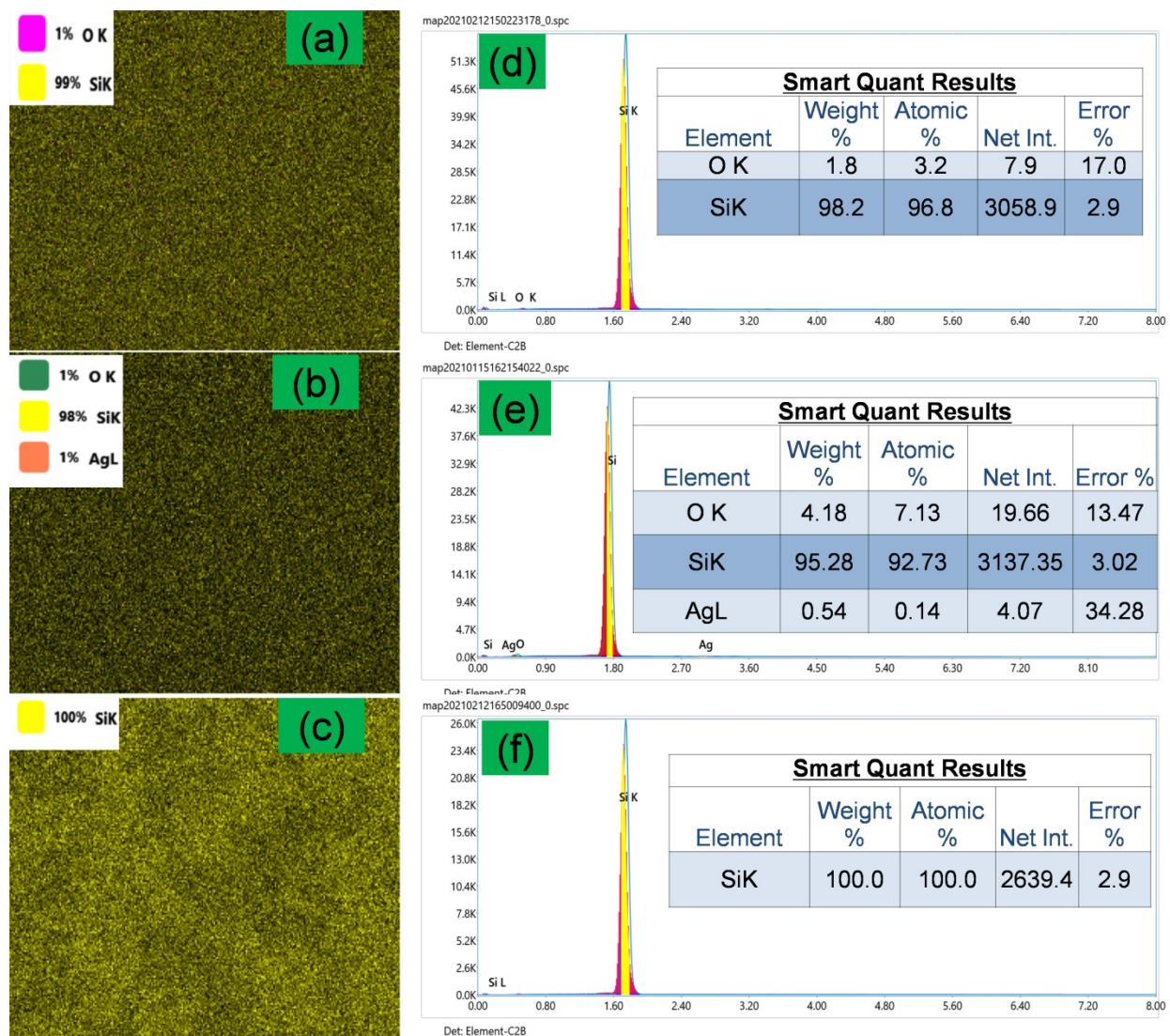


Fig S4. Elemental mapping of (a) 10S, (b) 20S and (c) 30S. EDX spectra of (d) 10S, (e) 20S and (f) 30S.

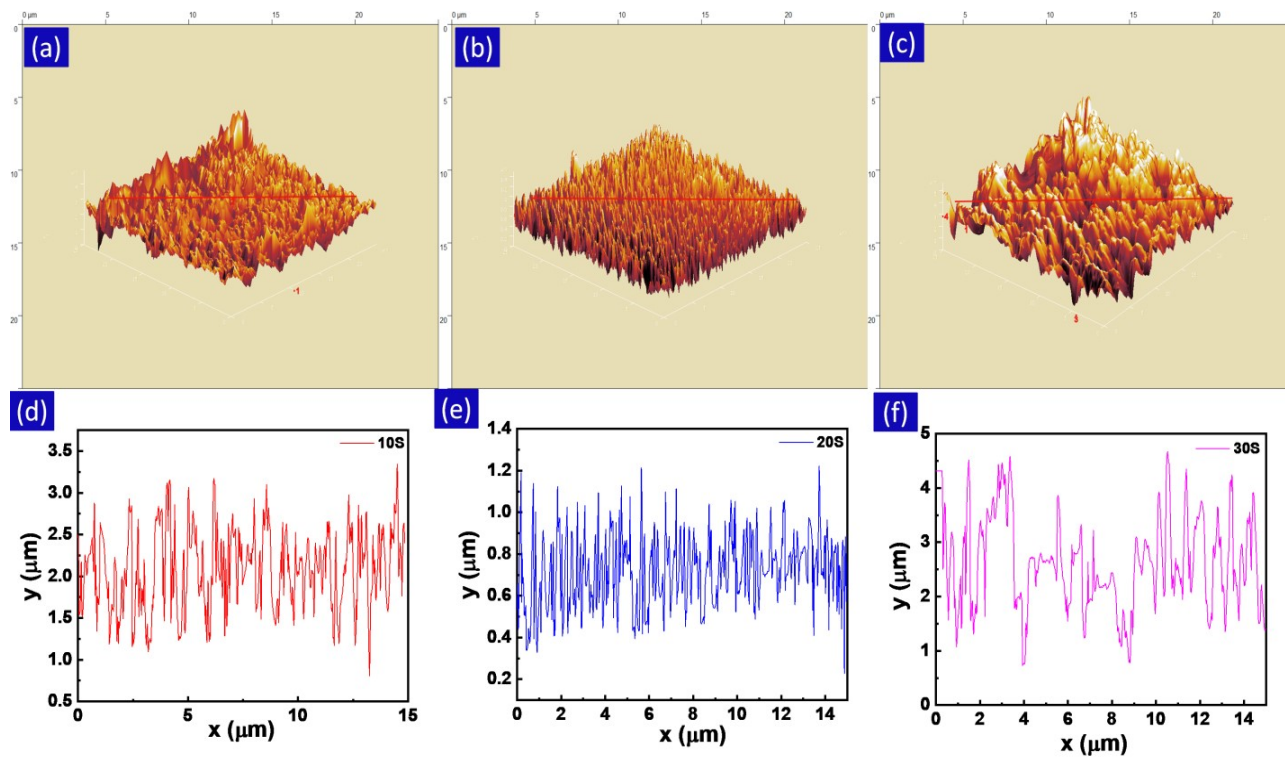


Fig. S5. (a), (b) and (c) 3D-AFM images and (e), (f) and (g) line profile for the calculation of the diameter of 10S, 20S and 30S, respectively.

